ELSEVIER

Applied Surface Science 92 (1996) 673–679

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Author index

Altman, M.S., see Luo, E.Z. 92 (1996) 331
Anderson, J.R., see Lu, C.R. 92 (1996) 404
Anderson, J.R., see Lu, C.R. 92 (1996) 543
Anderson, J.R., see Jen, J.Y. 92 (1996) 547
Anderson, W.A., see Chang, L.H. 92 (1996) 52
Aoki, T., M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka, Growth of ZnSe thin films by radical assisted MOCVD method 92 (1996) 132
Asahi, H., see Kim, J.H. 92 (1996) 566
Asami, K., see Kim, J.H. 92 (1996) 566
Asskali, A., see Reniers, F. 92 (1996) 35

Barbashev, E.A., see Skurat, V.E. 92 (1996) 441
Barthe, F., see Moison, J.M. 92 (1996) 526
Bauer, E., LEEM studies of the early stages of epitaxial growth 92 (1996) 20
Beloglazov, A.A., see Ksenevich, T.I. 92 (1996) 426
Beloglazov, A.A., see Uglov, S.A. 92 (1996) 656
Berbezier, I., see Derrien, J. 92 (1996) 311
Bhatnagar, M.C., see Sharma, R.K. 92 (1996) 647
Binau, K., see Guo, Q. 92 (1996) 513
Blatter, A., see Pimenov, S.M. 92 (1996) 106
Bögli, U., see Pimenov, S.M. 92 (1996) 106
Bogonin, I.A., A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin, Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment 92 (1996) 43
Borkowska, R., M. Siekierski and J. Przyłuski, An electrochemical impedance spectroscopy study of thin polymeric films 92 (1996) 447
Bugiel, E., see Zeindl, H.P. 92 (1996) 552
Burger, J., see Pimenov, S.M. 92 (1996) 106
Busch, E., see Haneman, D. 92 (1996) 484

Cai, Q., see Luo, E.Z. 92 (1996) 331
Chang, C.-Y., see Chang, T.-C. 92 (1996) 119
Chang, C.-Y., see Chang, T.-C. 92 (1996) 571
Chang, C.L., see Lu, C.R. 92 (1996) 404
Chang, C.P., see Huang, J.C.A. 92 (1996) 480
Chang, G.-W., see Tseng, B.-H. 92 (1996) 227
Chang, L.H. and W.A. Anderson, Stability of $BaTiO_3$ thin films on Si 92 (1996) 52
Chang, S.-Z., T.-C. Chang and S.-C. Lee, A method to tune the island size and improve the uniformity for the in situ formation of InGaAs quantum dots on GaAs 92 (1996) 70
Chang, S.J., see Lin, C.T. 92 (1996) 193
Chang, T.-C., see Chang, S.-Z. 92 (1996) 70
Chang, T.-C., W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei, Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition 92 (1996) 119
Chang, T.-C., W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei, Light emission from the porous boron δ-doped Si superlattice 92 (1996) 571
Chang, W.-D., see Ching, K.-M. 92 (1996) 471
Chang, W.-D. and T.-S. Chin, Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering 92 (1996) 475
Chen, B. and D. Haneman, Theory of dipole generation at cleaved semiconductor surfaces 92 (1996) 345
Chen, C.R. and L.J. Chen, Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures 92 (1996) 507
Chen, C.S., see Young, T.F. 92 (1996) 57
Chen, C.T., see Lee, C.H. 92 (1996) 124
Chen, F., see Horng, R.H. 92 (1996) 387
Chen, L.J., see Liu, C.S. 92 (1996) 84
Chen, L.J., see Lin, J.H. 92 (1996) 340
Chen, L.J., see Chen, C.R. 92 (1996) 507
Chen, P.-C., see Hwang, H.-L. 92 (1996) 180
Chen, P.-L., M.-Y. Tsai and J.-S. Kao, Low temperature growth of diamond-like films by cathodic arc plasma deposition 92 (1996) 30
Chen, W.S., see Lin, C.C. 92 (1996) 660
Cheng, C. and K. Kunc, First-principles calculations of Ga adatom structures for Ge(111) and Si(111) surfaces 92 (1996) 496

Cheng, H.-C., see Wang, F.-S. 92 (1996) 372
Cheng, H.-F., Structural and electrical properties of excimer laser deposited PLZT thin films 92 (1996) 378
Cheng, H.F., see Chuang, F.Y. 92 (1996) 452
Chin, T.-S., see Ching, K.-M. 92 (1996) 471
Chin, T.-S., see Chang, W.-D. 92 (1996) 475
Ching, K.-M., W.-D. Chang and T.-S. Chin, Effect of substrate–film interface on magnetic properties of Mn_4N films 92 (1996) 471
Cho, H.-C., Ge deposition from digermane on the Si(100)-(2 × 1) surface 92 (1996) 128
Chuang, F.Y., C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin, Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers 92 (1996) 452
Chung, W.F., see Luo, E.Z. 92 (1996) 331
Chyi, J.-I., see Lee, W.C. 92 (1996) 66
Coluzza, C., Ultra accurate measurements of interface parameters with free-electron laser 92 (1996) 267
Crisp, R.S., D. Haneman and R. Sabet-Dariani, Porous silicon studied by Si L_{23} soft X-ray emission 92 (1996) 198

Dai, B.-T., see Liu, C.-W. 92 (1996) 176
Delplancke, M.P., see Reniers, F. 92 (1996) 35
Derrien, J., I. Berbezier, A. Ronda and J.Y. Natoli, Interface phase transition as observed in ultra thin $FeSi_2$ epilayers 92 (1996) 311
Doi, K., see Kim, J.H. 92 (1996) 566
Dorofeev, Yu.I., see Skurat, V.E. 92 (1996) 441
Du, S.K., see Lu, C.R. 92 (1996) 543
Dutta, V., see Paulson, P.D. 92 (1996) 295

Eddrief, M., see Reqqass, H. 92 (1996) 357

Flores, F., see Rincón, R. 92 (1996) 216
Flores, F., see Saiz-Pardo, R. 92 (1996) 362
Fu, G.H., see Young, T.F. 92 (1996) 57
Fu, T., see Shern, C.S. 92 (1996) 74
Fuentes-Cabrera, M., see Rodríguez-Hernández, P. 92 (1996) 408
Fujiyasu, H., see Tatsuoka, H. 92 (1996) 382
Fukuda, Y., N. Sanada, M. Kuroda and Y. Suzuki, Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS 92 (1996) 212
Furukawa, Y., see Kayama, H. 92 (1996) 142

García-Vidal, F.J., see Rincón, R. 92 (1996) 216
Gérard, J.M., see Moison, J.M. 92 (1996) 526
Gonda, S., see Kim, J.H. 92 (1996) 566
Gong, Y.S., J.-C. Lin and C. Lee, Interdiffusion and reactions in the Cu/TiN/Si thin film system 92 (1996) 335
González-Diaz, M., see Rodríguez-Hernández, P. 92 (1996) 408
Gorelova, M.M., see Skurat, V.E. 92 (1996) 441
Gorska, M., see Jen, J.Y. 92 (1996) 547
Grigorenko, A.N. and P.I. Nikitin, Magnetostochastic resonance as a new method for investigations of surface and thin film magnetism 92 (1996) 466
Gu, G.-L., see Tseng, B.-H. 92 (1996) 227
Gu, G.-L., see Tseng, B.-H. 92 (1996) 412
Gui, L., see Guo, Q. 92 (1996) 513
Guo, Q., L. Guï, P.J. Møller and K. Binau, XPS, AES and LEED studies of Cu deposited on Cr_2O_3(0001) surfaces 92 (1996) 513

Hajto, J., B. McAuley, A.J. Snell, G.H.W. Milburn and A.E. Owen, Theory of room temperature quantized resistance steps in electroformed metal–a-Si:H–metal structures 92 (1996) 579
Hamakawa, Y., A technological evolution from bulk crystalline age to multilayered thin film age in optoelectronic devices 92 (1996) 1
Haneman, D., see Crisp, R.S. 92 (1996) 198
Haneman, D., see Chen, B. 92 (1996) 345
Haneman, D., N.S. McAlpine, E. Busch and C. Kaalund, Semiconductor bond rupture phenomena and surface properties 92 (1996) 484
Hashimoto, M., see Qiu, H. 92 (1996) 47
Hashimoto, Y., see Ogawa, Y. 92 (1996) 232
Hatanaka, Y., see Aoki, T. 92 (1996) 132
Hatanaka, Y., see Jayatissa, A.H. 92 (1996) 300
Hatanaka, Y., see Nakanishi, Y. 92 (1996) 400
Hayashi, K., see Nakamura, T. 92 (1996) 291
Higashiguchi, T., see Satoh, M. 92 (1996) 635
Hintermann, H.E., see Pimenov, S.M. 92 (1996) 106
Honda, F. and T. Saito, Tribochemical characterization of the lubrication film at the Si_3N_4/Si_3N_4 interface sliding in aqueous solutions 92 (1996) 651
Hong, Y., see Wei, Y. 92 (1996) 491
Horng, R.H., F. Chen, D.S. Wuu and T.Y. Lin, Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition 92 (1996) 387
Houzay, F., see Moison, J.M. 92 (1996) 526
Hsieh, J.T. and H.L. Hwang, AES and SRUPS studies on surface passivation of GaAs by $(NH_4)_2S_x$ sulfurization techniques 92 (1996) 222
Hsu, H.-Z., see Tseng, B.-H. 92 (1996) 412
Hsu, K.Y.J., see Hwang, H.-L. 92 (1996) 180
Hsu, K.Y.J., see Lee, C.H. 92 (1996) 621
Hsu, K.Y.J., see Lin, C.C. 92 (1996) 660
Hsu, M.-Y., see Chang, T.-C. 92 (1996) 571
Hsu, T.M., see Lee, W.C. 92 (1996) 66
Hu,, C.C., see Lee, M.K. 92 (1996) 159
Hua, T.H., see Ogawa, Y. 92 (1996) 232
Huang, G.-W., see Chang, T.-C. 92 (1996) 119

Huang, G.-W., see Chang, T.-C. 92 (1996) 571
Huang, J.C.A., Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee, Novel epitaxial growth and magnetotransport characterization of single crystal Co(11$\bar{2}$0)/Cr(100) superlattices on Mo buffer layers 92 (1996) 480
Huang, Y. and C. Lien, Voltage-tunable far-infrared photodetector with a very large tuning range 92 (1996) 537
Hwang, C.Z., see Lee, M.K. 92 (1996) 159
Hwang, H.L., see Wang, K.C. 92 (1996) 99
Hwang, H.-L., P.-C. Chen and K.Y.J. Hsu, Ultra-thin gate dielectrics grown by low-temperature processes for applications to ULSI devices 92 (1996) 180
Hwang, H.L., see Hsieh, J.T. 92 (1996) 222
Hwang, H.L., see Lin, C.C. 92 (1996) 660
Hwu, J.-G., see Lee, K.-C. 92 (1996) 204
Hwu, J.-G., see Jeng, M.-J. 92 (1996) 208
Hwu, Y., see Margaritondo, G. 92 (1996) 273

Ichinohe, T., see Shimasaki, M. 92 (1996) 617
Igari, Y., see Takagaki, T. 92 (1996) 287
Inoue, Y., see Sato, K. 92 (1996) 639
Isshiki, M., see Mochizuki, K. 92 (1996) 79
Ito, K., see Nakayama, N. 92 (1996) 171
Ito, K., see Ogawa, Y. 92 (1996) 232
Iwase, M., see Shimasaki, M. 92 (1996) 617
Iwatsuki, M., T. Sato and Y. Yamamoto, High-temperature STM for atomic processes on semiconductor surfaces 92 (1996) 321
Izumi, T., see Shimasaki, M. 92 (1996) 617

Jagadish, C., see Li, G. 92 (1996) 138
Jäger-Waldau, A., see Ogawa, Y. 92 (1996) 232
Jayatissa, A.H., M. Suzuki, Y. Nakanishi and Y. Hatanaka, Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films 92 (1996) 300
Jen, J.Y., T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska, Stimulated blue emission processes in $Zn_{1-x}Cd_xSe/ZnSe$ multi-quantum wells 92 (1996) 547
Jeng, M.-J., H.-S. Lin and J.-G. Hwu, Rapid thermal post-metallization annealing effect on thin gate oxides 92 (1996) 208
Jou, H., W. Tsang and A.M. Kriman, Effects of contact geometry in wide Hall bars 92 (1996) 585
Jung, T.-G., see Chang, T.-C. 92 (1996) 119
Jung, T.-G., see Chang, T.-C. 92 (1996) 571

Kaalund, C., see Haneman, D. 92 (1996) 484
Kalabina, N.A., see Ksenevich, T.I. 92 (1996) 426
Kanemitsu, Y., see Mimura, H. 92 (1996) 396
Kanemitsu, Y., see Mimura, H. 92 (1996) 598
Kao, J.-S., see Chen, P.-L. 92 (1996) 30
Karuzskii, A.L., see Bogonin, I.A. 92 (1996) 43
Karuzskii, A.L., N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin, Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high-T_c superconductor films 92 (1996) 457
Kayama, H., Y. Noda and Y. Furukawa, Growth of the thin film Cd–Si–As system by metalorganic chemical vapor deposition 92 (1996) 142
Kikuma, I., see Morisawa, Y. 92 (1996) 147
Kikuma, I., see Satoh, M. 92 (1996) 635
Kim, J.H., H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gonda, Improvement of optical properties of gas source MBE grown GaP/AlP short period superlattices 92 (1996) 566
Kirillova, T.A., see Sadygov, Z.Y. 92 (1996) 575
Kobayashi, J., see Nakamura, T. 92 (1996) 291
Konov, V.I., see Pimenov, S.M. 92 (1996) 106
Konov, V.I., see Uglov, S.A. 92 (1996) 656
Kriman, A.M., see Jou, H. 92 (1996) 585
Ksenevich, T.I., A.A. Beloglazov, P.I. Nikitin, N.A. Kalabina and S.Yu. Zaitsev, Study of biochemical reactions in thin organic films by means of evanescent optical wave 92 (1996) 426
Kuan, C.H., Noise characteristics of an infrared hot-electron transistor 92 (1996) 532
Kukushkin, S.A., see Sakalo, T.V. 92 (1996) 261
Kukushkin, S.A., see Sakalo, T.V. 92 (1996) 350
Kunc, K., see Cheng, C. 92 (1996) 496
Kuo, W.-K., J.-P. Wang and Y.-C. Ling, Structural characterization of $BaTiO_3$ films by sol–gel method using mono-substituting chelating agent 92 (1996) 155
Kurabayashi, T., see Nishizawa, J. 92 (1996) 89
Kuroda, M., see Fukuda, Y. 92 (1996) 212
Kusunoki, I., see Takagaki, T. 92 (1996) 287
Kuwabara, H., see Tatsuoka, H. 92 (1996) 382
Kwok, R.W.M., see Yan, H. 92 (1996) 61
Kyotani, T., see Mochizuki, K. 92 (1996) 79

Lacharme, J.-P., see Reqqass, H. 92 (1996) 357
Lai, W.-K., see Wang, F.-S. 92 (1996) 372
Landman, U. and W.D. Luedtke, Atomistic dynamics of interfacial processes: films, junctions and nanostructures 92 (1996) 237
Lebouché, N., see Moison, J.M. 92 (1996) 526
Lee, C., see Gong, Y.S. 92 (1996) 335
Lee, C.-H. and S.-Y. Tseng, In situ X-ray reflectivity measurement of thin film growth during vacuum deposition 92 (1996) 282
Lee, C.-P. and D.-C. Liu, High quality quantum dots fabricated by molecular beam epitaxy 92 (1996) 519
Lee, C.-P., see Chang, T.-C. 92 (1996) 571

Lee, C.H. and C.T. Chen, Characteristics of PECVD GaN thin films 92 (1996) 124
Lee, C.H. and L.Y. Lin, Characteristics of spray pyrolytic ZnO thin films 92 (1996) 163
Lee, C.H., see Huang, J.C.A. 92 (1996) 480
Lee, C.H., C.C. Yeh, C.H. Lee and K.Y.J. Hsu, Formation of bottom oxides in porous silicon films by anodic oxidation 92 (1996) 621
Lee, C.H., see Lee, C.H. 92 (1996) 621
Lee, G.S., see Lee, W.C. 92 (1996) 66
Lee, K.-C. and J.-G. Hwu, Application of irradiation-then-nitridation to improve the radiation hardness in MOS gate dielectrics 92 (1996) 204
Lee, K.C., see Lee, W.C. 92 (1996) 66
Lee, M.K., C.C. Hu, and C.Z. Hwang, The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy 92 (1996) 159
Lee, M.L., see Wuu, D.S. 92 (1996) 626
Lee, S.-C., see Chang, S.-Z. 92 (1996) 70
Lee, S.F., see Huang, J.C.A. 92 (1996) 480
Lee, W.C., T.M. Hsu, J.-I. Chyi, G.S. Lee, W.-H. Li and K.C. Lee, Characterization of low temperature GaAs grown by molecular beam epitaxy 92 (1996) 66
Leijala, A., see Pimenov, S.M. 92 (1996) 106
Leprince, L., see Moison, J.M. 92 (1996) 526
Le Thanh, V., see Reqqass, H. 92 (1996) 357
Lévy, F., see Wu, W.T. 92 (1996) 391
Li, A.L. and I. Shih, Investigation on origin of excess noise in superconducting and normal state BiSrCaCuO films 92 (1996) 461
Li, D.C., C.S. Yoo and C.Y. Sun, Tungsten absorber on silicon membrane 92 (1996) 665
Li, G. and C. Jagadish, Growth of Zn δ-doped $Al_xGa_{1-x}As$ ($x = 0$–0.65) by low pressure metal organic vapour phase epitaxy 92 (1996) 138
Li, W.-H., see Lee, W.C. 92 (1996) 66
Liao, S.Y., see Huang, J.C.A. 92 (1996) 480
Lie, D.Y.C., N.D. Theodore and J.H. Song, Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100) 92 (1996) 557
Lien, C., see Huang, Y. 92 (1996) 537
Lin, C.C., W.S. Chen, H.L. Hwang, K.Y.J. Hsu, H.K. Liou and K.N. Tu, Reliability study of sub-micron titanium silicide contacts 92 (1996) 660
Lin, C.T., S.J. Chang, D.K. Nayak and Y. Shiraki, The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers 92 (1996) 193
Lin, C.T., see Chuang, F.Y. 92 (1996) 452
Lin, H.-S., see Jeng, M.-J. 92 (1996) 208
Lin, I.N., see Chuang, F.Y. 92 (1996) 452
Lin, J.-C., see Gong, Y.S. 92 (1996) 335
Lin, J.H. and L.J. Chen, The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion 92 (1996) 340
Lin, L.Y., see Lee, C.H. 92 (1996) 163
Lin, S.-B., see Tseng, B.-H. 92 (1996) 412
Lin, T.Y., see Horng, R.H. 92 (1996) 387
Lin, T.Y., see Wuu, D.S. 92 (1996) 626
Ling, Y.-C., see Kuo, W.-K. 92 (1996) 155
Liou, C.H., see Lu, C.R. 92 (1996) 404
Liou, H.K., see Lin, C.C. 92 (1996) 660
Liou, Y., Textured diamond growth by microwave plasma chemical vapor deposition 92 (1996) 115
Liou, Y., see Huang, J.C.A. 92 (1996) 480
Liu, C.-W., B.-T. Dai and C.-F. Yeh, Post cleaning of chemical mechanical polishing process 92 (1996) 176
Liu, C.S. and L.J. Chen, Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si 92 (1996) 84
Liu, D.-C., see Lee, C.-P. 92 (1996) 519
Liu, J.F., see Young, T.F. 92 (1996) 57
Lokhande, C.D., see Mohite, U.K. 92 (1996) 151
Loubnin, E.N., see Pimenov, S.M. 92 (1996) 106
Lu, C.R., C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson, Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures 92 (1996) 404
Lu, C.R., S.K. Du, J.R. Anderson, D.R. Stone and R.A. Wilson, Photoreflectance study of $GaAs/Al_{0.3}Ga_{0.7}As$ resonant asymmetric double quantum wells with Si δ-doping in side barriers 92 (1996) 543
Luedtke, W.D., see Landman, U. 92 (1996) 237
Luo, E.Z., Q. Cai, W.F. Chung and M.S. Altman, Interface effects in melting of Pb clusters on the Cu(111) surface 92 (1996) 331
Maillat, M., see Pimenov, S.M. 92 (1996) 106
Margaritondo, G. and Y. Hwu, Photoemission spectromicroscopy and free electron laser spectroscopy of surfaces and interfaces 92 (1996) 273
Marzin, J.Y., see Moison, J.M. 92 (1996) 526
Masui, M., T. Ogawa and M. Takeuchi, Electrochromic behavior of amorphous cobaltphthalocyanine thin films 92 (1996) 421
Masui, M., M. Sasahara, T. Wada and M. Takeuchi, Gas sensitive properties of copperphthalocyanine thin films 92 (1996) 634
Matsuda, M., see Satoh, M. 92 (1996) 635
Matsumoto, S., see Satoh, M. 92 (1996) 635
Matsumoto, T., see Mimura, H. 92 (1996) 396

Matsumoto, T., see Mimura, H. 92 (1996) 598
Mauch, R.H., Electroluminescence in thin films 92 (1996) 589
McAlpine, N.S., see Haneman, D. 92 (1996) 484
McAuley, B., see Hajto, J. 92 (1996) 579
McElnea, A.E., see Morris, G.C. 92 (1996) 167
Mei, Y.-J., see Chang, T.-C. 92 (1996) 119
Mei, Y.-J., see Chang, T.-C. 92 (1996) 571
Melnik, N.N., see Bogonin, I.A. 92 (1996) 43
Melnik, N.N., see Karuzskii, A.L. 92 (1996) 457
Milburn, G.H.W., see Hajto, J. 92 (1996) 579
Mimura, H., see Nakamura, T. 92 (1996) 291
Mimura, H., T. Matsumoto and Y. Kanemitsu, PL properties of porous Si anodized with various light illuminations 92 (1996) 396
Mimura, H., T. Matsumoto and Y. Kanemitsu, Si-based optical devices using porous materials 92 (1996) 598
Mityagin, Yu.A., see Bogonin, I.A. 92 (1996) 43
Mochizuki, K., H. Oguri, T. Kyotani and M. Isshiki, Epitaxial growth of $ZnSe_x$-Te_{1-x} by the VPE method and its photoluminescence 92 (1996) 79
Mohite, U.K. and C.D. Lokhande, Electrosynthesis of yttrium chalcogenides from a non-aqueous bath 92 (1996) 151
Moison, J.M., L. Leprince, F. Barthe, F. Houzay, N. Lebouché, J.M. Gérard and J.Y. Marzin, Self-organized growth of InAs/GaAs quantum boxes 92 (1996) 526
Møller, P.J., see Guo, Q. 92 (1996) 513
Momose, Y., see Satoh, M. 92 (1996) 635
Mönch, W., Chemical trends of barrier heights in metal–semiconductor contacts: on the theory of the slope parameter 92 (1996) 367
Morawski, A., see Pohoryles, B. 92 (1996) 417
Morisaki, H., see Shimasaki, M. 92 (1996) 617
Morisawa, Y., I. Kikuma, N. Takayama and M. Takeuchi, Mirror polishing of InP wafer surfaces with NaOCl–citric acid 92 (1996) 147
Morita, M., see Aoki, T. 92 (1996) 132
Morris, G.C. and A.E. McElnea, Fluorine doped tin oxide films from spray pyrolysis of stannous fluoride solutions 92 (1996) 167
Morris, G.C. and R.J. Vanderveen, Solar cells from thin films prepared by periodic pulse electrodeposition 92 (1996) 630
Mujica, A., see Rodríguez-Hernández, P. 92 (1996) 408
Muñoz, A., see Rodríguez-Hernández, P. 92 (1996) 408
Muranoi, T., see Satoh, M. 92 (1996) 635
Murzin, V.N., see Bogonin, I.A. 92 (1996) 43
Murzin, V.N., see Karuzskii, A.L. 92 (1996) 457

Naito, S., see Nakanishi, Y. 92 (1996) 400
Nakai, H., see Qiu, H. 92 (1996) 47
Nakamura, T., K. Sasaki, K. Hayashi, H. Mimura and J. Kobayashi, Electron paramagnetic resonance measurements on porous silicon 92 (1996) 291
Nakamura, T., see Tatsuoka, H. 92 (1996) 382
Nakamura, T., see Nakanishi, Y. 92 (1996) 400
Nakanishi, Y., see Aoki, T. 92 (1996) 132
Nakanishi, Y., see Jayatissa, A.H. 92 (1996) 300
Nakanishi, Y., see Tatsuoka, H. 92 (1996) 382
Nakanishi, Y., S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka, The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films 92 (1996) 400
Nakayama, N. and K. Ito, Sprayed films of stannite Cu_2ZnSnS_4 92 (1996) 171
Natoli, J.Y., see Derrien, J. 92 (1996) 311
Nayak, D.K., see Lin, C.T. 92 (1996) 193
Nikiforov, A.P., see Skurat, V.E. 92 (1996) 441
Nikitin, P.I., see Ksenevich, T.I. 92 (1996) 426
Nikitin, P.I., see Grigorenko, A.N. 92 (1996) 466
Nilsson, S., see Zeindl, H.P. 92 (1996) 552
Nishizawa, J., H. Sakuraba and T. Kurabayashi, Surface reaction mechanism in MOCVD 92 (1996) 89
Noda, Y., see Kayama, H. 92 (1996) 142
Nomura, S., see Sato, K. 92 (1996) 639
Nozaki, S., see Shimasaki, M. 92 (1996) 617
Nozdrin, V.S., see Karuzskii, A.L. 92 (1996) 457

Obraztsova, E.D., see Pimenov, S.M. 92 (1996) 106
Ogawa, T., see Masui, M. 92 (1996) 421
Ogawa, Y., A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito, Influence of KCN treatment on $CuInS_2$ thin films 92 (1996) 232
Ogura, T., see Kim, J.H. 92 (1996) 566
Oguri, H., see Mochizuki, K. 92 (1996) 79
Ohbuchi, T., see Qiu, H. 92 (1996) 47
Oka, Y., see Jen, J.Y. 92 (1996) 547
Orlikovsky, A.A., see Bogonin, I.A. 92 (1996) 43
Oshita, M., see Tatsuoka, H. 92 (1996) 382
Owen, A.E., see Hajto, J. 92 (1996) 579

Paulson, P.D. and V. Dutta, Photoellipsometric studies on CdTe thin films 92 (1996) 295
Perestoronin, A.V., see Bogonin, I.A. 92 (1996) 43
Perestoronin, A.V., see Karuzskii, A.L. 92 (1996) 457
Pertsyn, A.I., see Skurat, V.E. 92 (1996) 441
Pimenov, S.M., A.A. Smolin, E.D. Obraztsova, V.I. Konov, U. Bögli, A. Blatter, E.N. Loubnin, M. Maillat, A. Leijala, J. Burger and H.E. Hintermann, Tribological properties of smooth diamond films 92 (1996) 106
Pohoryles, B. and A. Morawski, Surface charge transfer in plastically deformed Si 92 (1996) 417
Przyłuski, J., see Borkowska, R. 92 (1996) 447

Qiu, C.X., see Qiu, S.N. 92 (1996) 306
Qiu, H., T. Ohbuchi, H. Nakai and M. Hashimoto, Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001) 92 (1996) 47
Qiu, S.N., C.X. Qiu and I. Shih, Diffusion length measurements on electrode-posited $CuInSe_2$ cells 92 (1996) 306

Reniers, F., M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay, Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO-Experimental parameters and epitaxy 92 (1996) 35
Reqqass, H., J.-P. Lacharme, C.A. Sébenne, M. Eddrief and V. Le Thanh, Surface electronic properties of GaSe-covered Si(111) upon UHV thermal desorption of the GaSe epitaxial layer 92 (1996) 357
Rincón, R., F.J. García-Vidal and F. Flores, A theoretical analysis of the molecular and dissociative adsorption of H_2O on GaAs(110) 92 (1996) 216
Rincón, R., see Saiz-Pardo, R. 92 (1996) 362
Rodríguez-Hernández, P., M. González-Diaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz, Band lineup modification by Ge interlayer deposition at II–VI/III–V semiconductor heterojunctions 92 (1996) 408
Ronda, A., see Derrien, J. 92 (1996) 311
Rooryck, V., see Reniers, F. 92 (1996) 35

Sabet-Dariani, R., see Crisp, R.S. 92 (1996) 198
Sadygov, Z.Y., I.M. Zheleznykh and T.A. Kirillova, Novel light quantum and nuclear particle detectors based on the avalanche metal–resistivity layer–semiconductor structure 92 (1996) 575
Saito, T., see Honda, F. 92 (1996) 651
Saiz-Pardo, R., R. Rincón and F. Flores, Schottky barrier formation for passivated semiconductor surfaces 92 (1996) 362
Sakalo, T.V. and S.A. Kukushkin, Phenomenological approach in modeling of thin film nucleation from the liquid phase 92 (1996) 261
Sakalo, T.V. and S.A. Kukushkin, Coalescence of cylindrical islands on the crystal surface accompanied by correlated changes of their heights and radii 92 (1996) 350
Sakuraba, H., see Nishizawa, J. 92 (1996) 89
Sanada, N., see Fukuda, Y. 92 (1996) 212
Sasahara, M., see Masui, M. 92 (1996) 634
Sasaki, K., see Nakamura, T. 92 (1996) 291
Sato, K., S. Nomura and Y. Inoue, Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell 92 (1996) 639
Sato, T., see Iwatsuki, M. 92 (1996) 321
Satoh, M., S. Matsumoto, T. Higashiguchi, M. Matsuda, T. Muranoi, I. Kikuma, Y. Momose and M. Takeuchi, Surface fluorination of electrophotographic photoreceptors by plasma treatment for contact charging with a wet polymer roller 92 (1996) 635
Schmid, P.E., see Wu, W.T. 92 (1996) 391
Schock, H.W., Thin film photovoltaics 92 (1996) 606
Sébenne, C.A., see Reqqass, H. 92 (1996) 357
Sharma, G.L., see Sharma, R.K. 92 (1996) 647
Sharma, R.K., M.C. Bhatnagar and G.L. Sharma, Effect of Nb metal ion in TiO_2 oxygen gas sensor 92 (1996) 647
Shern, C.S., J.S. Tsay and T. Fu, Growth mechanism of Ni on Pt(110) at low temperature 92 (1996) 74
Shih, I., see Qiu, S.N. 92 (1996) 306
Shih, I., see Li, A.L. 92 (1996) 461
Shimaoka, G., see Nakanishi, Y. 92 (1996) 400
Shimasaki, M., Y. Show, M. Iwase, T. Izumi, T. Ichinohe, S. Nozaki and H. Morisaki, Correlation between light emission and dangling bonds in porous silicon 92 (1996) 617
Shiraki, Y., see Lin, C.T. 92 (1996) 193
Show, Y., see Shimasaki, M. 92 (1996) 617
Shub, V.E., see Uglov, S.A. 92 (1996) 656
Siekierski, M., see Borkowska, R. 92 (1996) 447
Skurat, V.E., E.A. Barbashev, Yu.I. Dorofeev, A.P. Nikiforov, M.M. Gorelova and A.I. Pertsyn, Simulation of polymer film and surface behaviour in a space environment 92 (1996) 441
Smolin, A.A., see Pimenov, S.M. 92 (1996) 106
Snell, A.J., see Hajto, J. 92 (1996) 579
Song, J.H., see Lie, D.Y.C. 92 (1996) 557
Soukiassian, P., see Spiess, L. 92 (1996) 501
Souma, I., see Jen, J.Y. 92 (1996) 547
Spiess, L., E. Wimmer and P. Soukiassian, Structural properties of Na adsorbed on a Ge(100)2 × 1 surface: all electron, ab initio, density functional, cluster calculations 92 (1996) 501
Stone, D.R., see Lu, C.R. 92 (1996) 404
Stone, D.R., see Lu, C.R. 92 (1996) 543
Sun, C.Y., see Chuang, F.Y. 92 (1996) 452
Sun, C.Y., see Li, D.C. 92 (1996) 665
Suzuki, M., see Jayatissa, A.H. 92 (1996) 300
Suzuki, Y., see Fukuda, Y. 92 (1996) 212
Sverbil, P.P., see Bogonin, I.A. 92 (1996) 43
Szklarczyk, M., In situ radiotracer method for study of adsorption on semiconductor single crystal surfaces 92 (1996) 431

Takagaki, T., Y. Igari, T. Takaoka and I. Kusunoki, XPS study of the reaction of the Si(100) surface with a C_2H_4 beam 92 (1996) 287
Takaoka, T., see Takagaki, T. 92 (1996) 287
Takayama, N., see Morisawa, Y. 92 (1996) 147
Takeuchi, M., see Morisawa, Y. 92 (1996) 147
Takeuchi, M., see Masui, M. 92 (1996) 421
Takeuchi, M., see Masui, M. 92 (1996) 634
Takeuchi, M., see Satoh, M. 92 (1996) 635
Tang, T.B., Computer simulation of nucleation on (001) Kossel crystal surface with and without diffusion 92 (1996) 257
Tatsuoka, H., H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu, Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy 92 (1996) 382
Teixeira Rabelo, J.N., see Zubov, V.I. 92 (1996) 436
Theodore, N.D., see Lie, D.Y.C. 92 (1996) 557
Tkachenko, S.D., see Bogonin, I.A. 92 (1996) 43
Tretiakov, N.P., see Zubov, V.I. 92 (1996) 436
Tsai, M.-J., see Wang, F.-S. 92 (1996) 372
Tsai, M.-Y., see Chen, P.-L. 92 (1996) 30
Tsai, W.-C., see Chang, T.-C. 92 (1996) 119
Tsai, W.-C., see Chang, T.-C. 92 (1996) 571
Tsang, W., see Jou, H. 92 (1996) 585
Tsay, J.S., see Shern, C.S. 92 (1996) 74
Tseng, B.-H., G.-W. Chang and G.-L. Gu, Surfactant modified growth of $CuInSe_2$ thin films 92 (1996) 227
Tseng, B.-H., S.-B. Lin, G.-L. Gu and H.-Z. Hsu, Interface of $CuIn_{1-x}Ga_xSe_2$/GaAs heterostructure 92 (1996) 412
Tseng, S.-Y., see Lee, C.-H. 92 (1996) 282
Tsikunov, A.V., see Bogonin, I.A. 92 (1996) 43
Tsong, I.S.T., see Wei, Y. 92 (1996) 491
Tsutsumi, T., see Jen, J.Y. 92 (1996) 547
Tu, K.N., see Lin, C.C. 92 (1996) 660

Uglov, S.A., V.E. Shub, A.A. Beloglazov and V.I. Konov, Carbon nitride – prospects for ultimate performance of superhard materials 92 (1996) 656

Vanderveen, R.J., see Morris, G.C. 92 (1996) 630
Van Sinay, O., see Reniers, F. 92 (1996) 35
Vidali, G. and H. Zeng, Recent advances in island and multilayer growth of metals on metals far from equilibrium 92 (1996) 11
Volchkov, N.A., see Bogonin, I.A. 92 (1996) 43
Volchkov, N.A., see Karuzskii, A.L. 92 (1996) 457

Wada, T., see Masui, M. 92 (1996) 634
Wang, F.-S., M.-J. Tsai, W.-K. Lai and H.-C. Cheng, Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films 92 (1996) 372
Wang, J.-P., see Kuo, W.-K. 92 (1996) 155
Wang, K.C., T.R. Yew and H.L. Hwang, Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications 92 (1996) 99
Wei, Y., Y. Hong and I.S.T. Tsong, Oxygen etching of the Si(100)-(2 × 1) surface 92 (1996) 491
Wickramanayaka, S., see Aoki, T. 92 (1996) 132
Wilson, R.A., see Lu, C.R. 92 (1996) 404
Wilson, R.A., see Lu, C.R. 92 (1996) 543
Wimmer, E., see Spiess, L. 92 (1996) 501
Wong, S.P., see Yan, H. 92 (1996) 61
Wu, C.C., see Young, T.F. 92 (1996) 57
Wu, W.T., P.E. Schmid and F. Lévy, Structural and optical properties of $Pd_{1-x}In_x$ thin films 92 (1996) 391
Wuu, D.S., see Horng, R.H. 92 (1996) 387
Wuu, D.S., M.L. Lee and T.Y. Lin, Properties of multilayered thin films for thermal ink-jet printing devices 92 (1996) 626

Yamamoto, Y., see Iwatsuki, M. 92 (1996) 321
Yan, H., R.W.M. Kwok and S.P. Wong, XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source 92 (1996) 61
Yang, W.T., see Huang, J.C.A. 92 (1996) 480
Yao, Y.D., see Huang, J.C.A. 92 (1996) 480
Yeh, C.-F., see Liu, C.-W. 92 (1996) 176
Yeh, C.C., see Lee, C.H. 92 (1996) 621
Yeh, W.-K., see Chang, T.-C. 92 (1996) 119
Yeh, W.-K., see Chang, T.-C. 92 (1996) 571
Yew, T.R., see Wang, K.C. 92 (1996) 99
Yoo, C.S., see Li, D.C. 92 (1996) 665
Young, T.F., J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen, Study of Ag thin films deposited on porous silicon 92 (1996) 57

Zaitsev, S.Yu., see Ksenevich, T.I. 92 (1996) 426
Zeindl, H.P., S. Nilsson and E. Bugiel, Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements 92 (1996) 552
Zeng, H., see Vidali, G. 92 (1996) 11
Zheleznykh, I.M., see Sadygov, Z.Y. 92 (1996) 575
Zhurkin, B.G., see Bogonin, I.A. 92 (1996) 43
Zhurkin, B.G., see Karuzskii, A.L. 92 (1996) 457
Zubov, V.I., N.P. Tretiakov and J.N. Teixeira Rabelo, Microscopic theory of atomic properties of the surfaces of anharmonic crystals. Singular faces of fullerite C_{60} 92 (1996) 436

ELSEVIER

Applied Surface Science 92 (1996) 680–700

applied surface science

Subject index

Ablation

Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment, I.A. Bogonin, A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin 92 (1996) 43

Structural and electrical properties of excimer laser deposited PLZT thin films, H.-F. Cheng 92 (1996) 378

Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452

Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high-T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457

Carbon nitride – prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656

Alkali metals

Structural properties of Na adsorbed on a Ge(100)2×1 surface: all electron, ab initio, density functional, cluster calculations, L. Spiess, E. Wimmer and P. Soukiassian 92 (1996) 501

Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell, K. Sato, S. Nomura and Y. Inoue 92 (1996) 639

Alloys

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35

Aluminium

Growth of Zn δ-doped $Al_xGa_{1-x}As$ (x = 0–0.65) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish 92 (1996) 138

Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza 92 (1996) 267

In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282

Photoreflectance study of $GaAs/Al_{0.3}Ga_{0.7}As$ resonant asymmetric double quantum wells with Si δ-doping in side barriers, C.R. Lu, S.K. Du, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 543

Improvement of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gonda 92 (1996) 566

Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wuu, M.L. Lee and T.Y. Lin 92 (1996) 626

Annealing

Rapid thermal post-metallization annealing effect on thin gate oxides, M.-J. Jeng, H.-S. Lin and J.-G. Hwu 92 (1996) 208

Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films, A.H. Jayatissa, M. Suzuki, Y. Nakanishi and Y. Hatanaka 92 (1996) 300

Antimony

Surfactant modified growth of $CuInSe_2$ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227

Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382

Arc evaporation

Low temperature growth of diamond-like films by cathodic arc plasma deposition, P.-L. Chen, M.-Y. Tsai and J.-S. Kao 92 (1996) 30
XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong 92 (1996) 61

Arsenic

Growth of the thin film Cd–Si–As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404

Auger electron spectroscopy

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74
Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128
The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212
AES and SRUPS studies on surface passivation of GaAs by $(NH_4)_2S_x$ sulfurization techniques, J.T. Hsieh and H.L. Hwang 92 (1996) 222
Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
XPS, AES and LEED studies of Cu deposited on Cr_2O_3(0001) surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513

Barium

Stability of $BaTiO_3$ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
Structural characterization of $BaTiO_3$ films by sol–gel method using mono-substituting chelating agent, W.-K. Kuo, J.-P. Wang and Y.-C. Ling 92 (1996) 155
Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452

Borides

Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wuu, M.L. Lee and T.Y. Lin 92 (1996) 626

Boron

Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wuu and T.Y. Lin 92 (1996) 387

Cadmium

Growth of the thin film Cd–Si–As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
Stimulated blue emission processes in $Zn_{1-x}Cd_xSe/ZnSe$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547

Cadmium sulphide

Solar cells from thin films prepared by periodic pulse electrodeposition, G.C. Morris and R.J. Vanderveen 92 (1996) 630

Cadmium telluride

Photoellipsometric studies on CdTe thin films, P.D. Paulson and V. Dutta 92 (1996) 295
Thin film photovoltaics, H.W. Schock 92 (1996) 606
Solar cells from thin films prepared by periodic pulse electrodeposition, G.C. Morris and R.J. Vanderveen 92 (1996) 630

Carbides

XPS study of the reaction of the Si(100) surface with a C_2H_4 beam, T. Takagaki, Y. Igari, T. Takaoka and I. Kusunoki 92 (1996) 287

Carbon

Microscopic theory of atomic properties of the surfaces of anharmonic crystals. Singular faces of fullerite C_{60}, V.I. Zubov, N.P. Tretiakov and J.N. Teixeira Rabelo 92 (1996) 436
Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high-T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457
Carbon nitride – prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656

Chemical vapour deposition

Surface reaction mechanism in MOCVD, J. Nishizawa, H. Sakuraba and T. Kurabayashi 92 (1996) 89
Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
Tribological properties of smooth diamond films, S.M. Pimenov, A.A. Smolin, E.D. Obraztsova, V.I. Konov, U. Bögli, A. Blatter, E.N. Loubnin, M. Maillat, A. Leijala, J. Burger and H.E. Hintermann 92 (1996) 106
Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128
Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka 92 (1996) 132
The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
Ultra-thin gate dielectrics grown by low-temperature processes for applications to ULSI devices, H.-L. Hwang, P.-C. Chen and K.Y.J. Hsu 92 (1996) 180
The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wuu and T.Y. Lin 92 (1996) 387
Tungsten absorber on silicon membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665

Chromium

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F.

Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Novel epitaxial growth and magnetotransport characterization of single crystal Co(11$\bar{2}$0)/Cr(100) superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480
XPS, AES and LEED studies of Cu deposited on Cr_2O_3(0001) surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513

Cobalt

Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
Novel epitaxial growth and magnetotransport characterization of single crystal Co(11$\bar{2}$0)/Cr(100) superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480

Copper

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
Sprayed films of stannite Cu_2ZnSnS_4, N. Nakayama and K. Ito 92 (1996) 171
Surfactant modified growth of $CuInSe_2$ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
Influence of KCN treatment on $CuInS_2$ thin films, Y. Ogawa, A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232
Diffusion length measurements on electrodeposited $CuInSe_2$ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
Interface effects in melting of Pb clusters on the Cu(111) surface, E.Z. Luo, Q. Cai, W.F. Chung and M.S. Altman 92 (1996) 331
Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
Interface of $CuIn_{1-x}Ga_xSe_2$/GaAs heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412
XPS, AES and LEED studies of Cu deposited on Cr_2O_3(0001) surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513
Thin film photovoltaics, H.W. Schock 92 (1996) 606
Gas sensitive properties of copperphthalocyanine thin films, M. Masui, M. Sasahara, T. Wada and M. Takeuchi 92 (1996) 634

Corrosion

Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452

Deuterium

Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128

Diamond

Low temperature growth of diamond-like films by cathodic arc plasma deposition, P.-L. Chen, M.-Y. Tsai and J.-S. Kao 92 (1996) 30
Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment, I.A. Bogonin, A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin 92 (1996) 43
Tribological properties of smooth diamond films, S.M. Pimenov, A.A. Smolin, E.D. Obraztsova, V.I. Konov, U. Bögli, A. Blatter, E.N. Loubnin, M. Maillat, A. Leijala, J. Burger and H.E. Hintermann 92 (1996) 106
Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high-T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457

Doping effects

Growth of Zn δ-doped $Al_xGa_{1-x}As$ (x = 0–0.65) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish 92 (1996) 138

Fluorine doped tin oxide films from spray pyrolysis of stannous fluoride solutions, G.C. Morris and A.E. McElnea 92 (1996) 167
Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wuu and T.Y. Lin 92 (1996) 387
Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
Light emission from the porous boron δ-doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571
Effect of Nb metal ion in TiO_2 oxygen gas sensor, R.K. Sharma, M.C. Bhatnagar and G.L. Sharma 92 (1996) 647

Electrical properties

Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
Stability of $BaTiO_3$ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
Diffusion length measurements on electrodeposited $CuInSe_2$ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
Structural and electrical properties of excimer laser deposited PLZT thin films, H.-F. Cheng 92 (1996) 378
An electrochemical impedance spectroscopy study of thin polymeric films, R. Borkowska, M. Siekierski and J. Przyłuski 92 (1996) 447
Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
Noise characteristics of an infrared hot-electron transistor, C.H. Kuan 92 (1996) 532
Effect of Nb metal ion in TiO_2 oxygen gas sensor, R.K. Sharma, M.C. Bhatnagar and G.L. Sharma 92 (1996) 647

Electron diffraction

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
Novel epitaxial growth and magnetotransport characterization of single crystal $Co(11\bar{2}0)/Cr(100)$ superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480
Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507

Electron microscopy

LEEM studies of the early stages of epitaxial growth, E. Bauer 92 (1996) 20
Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47

Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
A method to tune the island size and improve the uniformity for the in situ formation of InGaAs quantum dots on GaAs, S.-Z. Chang, T.-C. Chang and S.-C. Lee 92 (1996) 70
Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
Electrosynthesis of yttrium chalcogenides from a non-aqueous bath, U.K. Mohite and C.D. Lokhande 92 (1996) 151
Characteristics of spray pyrolytic ZnO thin films, C.H. Lee and L.Y. Lin 92 (1996) 163
Interface phase transition as observed in ultra thin $FeSi_2$ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
Interface effects in melting of Pb clusters on the Cu(111) surface, E.Z. Luo, Q. Cai, W.F. Chung and M.S. Altman 92 (1996) 331
The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
Interface of $CuIn_{1-x}Ga_xSe_2/GaAs$ heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412
Effect of substrate–film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507
Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
Light emission from the porous boron δ-doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571
Tribochemical characterization of the lubrication film at the Si_3N_4/Si_3N_4 interface sliding in aqueous solutions, F. Honda and T. Saito 92 (1996) 651

Electron spin resonance

Electron paramagnetic resonance measurements on porous silicon, T. Nakamura, K. Sasaki, K. Hayashi, H. Mimura and J. Kobayashi 92 (1996) 291

Ellipsometry

Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films, A.H. Jayatissa, M. Suzuki, Y. Nakanishi and Y. Hatanaka 92 (1996) 300
Structural and optical properties of $Pd_{1-x}In_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391

Emission

Photoellipsometric studies on CdTe thin films, P.D. Paulson and V. Dutta 92 (1996) 295

Epitaxy

Recent advances in island and multilayer growth of metals on metals far from equilibrium, G. Vidali and H. Zeng 92 (1996) 11
LEEM studies of the early stages of epitaxial growth, E. Bauer 92 (1996) 20
Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35

Characterization of low temperature GaAs grown by molecular beam epitaxy, W.C. Lee, T.M. Hsu, J.-I. Chyi, G.S. Lee, W.-H. Li and K.C. Lee 92 (1996) 66
Epitaxial growth of $ZnSe_xTe_{1-x}$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79
Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
Surface reaction mechanism in MOCVD, J. Nishizawa, H. Sakuraba and T. Kurabayashi 92 (1996) 89
Growth of Zn δ-doped $Al_xGa_{1-x}As$ (x = 0–0.65) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish 92 (1996) 138
The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
Surfactant modified growth of $CuInSe_2$ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
Interface phase transition as observed in ultra thin $FeSi_2$ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
Surface electronic properties of GaSe-covered Si(111) upon UHV thermal desorption of the GaSe epitaxial layer, H. Reqqass, J.-P. Lacharme, C.A. Sébenne, M. Eddrief and V. Le Thanh 92 (1996) 357
Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404
Band lineup modification by Ge interlayer deposition at II–VI/III–V semiconductor heterojunctions, P. Rodríguez-Hernández, M. González-Diaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz 92 (1996) 408
Interface of $CuIn_{1-x}Ga_xSe_2$/GaAs heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412
Novel epitaxial growth and magnetotransport characterization of single crystal Co(11$\bar{2}$0)/Cr(100) superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480
High quality quantum dots fabricated by molecular beam epitaxy, C.-P. Lee and D.-C. Liu 92 (1996) 519
Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
Improvement of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gonda 92 (1996) 566

Etching

Oxygen etching of the Si(100)-(2 × 1) surface, Y. Wei, Y. Hong and I.S.T. Tsong 92 (1996) 491

Evaporation

In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282
The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
Electrochromic behavior of amorphous cobaltphthalocyanine thin films, M. Masui, T. Ogawa and M. Takeuchi 92 (1996) 421
Gas sensitive properties of copperphthalocyanine thin films, M. Masui, M. Sasahara, T. Wada and M. Takeuchi 92 (1996) 634

Fullerenes

Microscopic theory of atomic properties of the surfaces of anharmonic crystals. Singular faces of fullerite C_{60}, V.I. Zubov, N.P. Tretiakov and J.N. Teixeira Rabelo 92 (1996) 436

Gallium

Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
First-principles calculations of Ga adatom structures for Ge(111) and Si(111) surfaces, C. Cheng and K. Kunc 92 (1996) 496

Gallium arsenide

Characterization of low temperature GaAs grown by molecular beam epitaxy, W.C. Lee, T.M. Hsu, J.-I. Chyi, G.S. Lee, W.-H. Li and K.C. Lee 92 (1996) 66

A method to tune the island size and improve the uniformity for the in situ formation of InGaAs quantum dots on GaAs, S.-Z. Chang, T.-C. Chang and S.-C. Lee 92 (1996) 70
Surface reaction mechanism in MOCVD, J. Nishizawa, H. Sakuraba and T. Kurabayashi 92 (1996) 89
Growth of Zn δ-doped $Al_xGa_{1-x}As$ (x = 0–0.65) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish 92 (1996) 138
The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
A theoretical analysis of the molecular and dissociative adsorption of H_2O on GaAs(110), R. Rincón, F.J. García-Vidal and F. Flores 92 (1996) 216
AES and SRUPS studies on surface passivation of GaAs by $(NH_4)_2S_x$ sulfurization techniques, J.T. Hsieh and H.L. Hwang 92 (1996) 222
Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza 92 (1996) 267
Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404
Band lineup modification by Ge interlayer deposition at II–VI/III–V semiconductor heterojunctions, P. Rodríguez-Hernández, M. González-Diaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz 92 (1996) 408
Interface of $CuIn_{1-x}Ga_xSe_2$/GaAs heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412
High quality quantum dots fabricated by molecular beam epitaxy, C.-P. Lee and D.-C. Liu 92 (1996) 519
Self-organized growth of InAs/GaAs quantum boxes, J.M. Moison, L. Leprince, F. Barthe, F. Houzay, N. Lebouché, J.M. Gérard and J.Y. Marzin 92 (1996) 526
Photoreflectance study of GaAs/$Al_{0.3}Ga_{0.7}As$ resonant asymmetric double quantum wells with Si δ-doping in side barriers, C.R. Lu, S.K. Du, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 543

Gallium phosphide

Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212
Improvement of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gonda 92 (1996) 566

Gallium selenide

Surface electronic properties of GaSe-covered Si(111) upon UHV thermal desorption of the GaSe epitaxial layer, H. Reqqass, J.-P. Lacharme, C.A. Sébenne, M. Eddrief and V. Le Thanh 92 (1996) 357

Germanium

Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128
The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza 92 (1996) 267
Band lineup modification by Ge interlayer deposition at II–VI/III–V semiconductor heterojunctions, P. Rodríguez-Hernández, M. González-Diaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz 92 (1996) 408
First-principles calculations of Ga adatom structures for Ge(111) and Si(111) surfaces, C. Cheng and K. Kunc 92 (1996) 496
Structural properties of Na adsorbed on a Ge(100)2 × 1 surface: all electron, ab initio, density functional, cluster calculations, L. Spiess, E. Wimmer and P. Soukiassian 92 (1996) 501
Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557

Gold

Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507

Hafnium

Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wuu, M.L. Lee and T.Y. Lin 92 (1996) 626

Hall effect

Effects of contact geometry in wide Hall bars, H. Jou, W. Tsang and A.M. Kriman 92 (1996) 585

Halogenides

The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400

Heterostructures

Interface of $CuIn_{1-x}Ga_xSe_2/GaAs$ heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412

Hydrocarbons

XPS study of the reaction of the Si(100) surface with a C_2H_4 beam, T. Takagaki, Y. Igari, T. Takaoka and I. Kusunoki 92 (1996) 287

In situ radiotracer method for study of adsorption on semiconductor single crystal surfaces, M. Szklarczyk 92 (1996) 431

Hydrogen

Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128

Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212

Theory of room temperature quantized resistance steps in electroformed metal–a-Si:H–metal structures, J. Hajto, B. McAuley, A.J. Snell, G.H.W. Milburn and A.E. Owen 92 (1996) 579

Indium

A method to tune the island size and improve the uniformity for the in situ formation of InGaAs quantum dots on GaAs, S.-Z. Chang, T.-C. Chang and S.-C. Lee 92 (1996) 70

Surfactant modified growth of $CuInSe_2$ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227

Influence of KCN treatment on $CuInS_2$ thin films, Y. Ogawa, A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232

Diffusion length measurements on electrodeposited $CuInSe_2$ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306

Structural and optical properties of $Pd_{1-x}In_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391

Interface of $CuIn_{1-x}Ga_xSe_2/GaAs$ heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412

Thin film photovoltaics, H.W. Schock 92 (1996) 606

Indium arsenide

Self-organized growth of InAs/GaAs quantum boxes, J.M. Moison, L. Leprince, F. Barthe, F. Houzay, N. Lebouché, J.M. Gérard and J.Y. Marzin 92 (1996) 526

Indium phosphide

Mirror polishing of InP wafer surfaces with NaOCl–citric acid, Y. Morisawa, I. Kikuma, N. Takayama and M. Takeuchi 92 (1996) 147

Interfaces

Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza 92 (1996) 267

Interface effects in melting of Pb clusters on the Cu(111) surface, E.Z. Luo, Q. Cai, W.F. Chung and M.S. Altman 92 (1996) 331

Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404

Interface of $CuIn_{1-x}Ga_xSe_2/GaAs$ heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412

Effect of substrate–film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471

Ion implantation

XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong 92 (1996) 61

Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557

Tungsten absorber on silicon membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665

Ion scattering

Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557

Iron

Interface phase transition as observed in ultra thin $FeSi_2$ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311

Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475

Laser processing

Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment, I.A. Bogonin, A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sverbil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin 92 (1996) 43

Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films, A.H. Jayatissa, M. Suzuki, Y. Nakanishi and Y. Hatanaka 92 (1996) 300

Structural and electrical properties of excimer laser deposited PLZT thin films, H.-F. Cheng 92 (1996) 378

Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452

Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high-T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457

Carbon nitride – prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656

Lead

Interface effects in melting of Pb clusters on the Cu(111) surface, E.Z. Luo, Q. Cai, W.F. Chung and M.S. Altman 92 (1996) 331

Low energy electron diffraction

Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74

Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212

XPS, AES and LEED studies of Cu deposited on $Cr_2O_3(0001)$ surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513

Luminescence

Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57

Epitaxial growth of $ZnSe_xTe_{1-x}$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79

The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159

PL properties of porous Si anodized with various light illuminations, H. Mimura, T. Matsumoto and Y. Kanemitsu 92 (1996) 396

The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400

High quality quantum dots fabricated by molecular beam epitaxy, C.-P. Lee and D.-C. Liu 92 (1996) 519

Stimulated blue emission processes in $Zn_{1-x}Cd_xSe/ZnSe$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547

Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552

Light emission from the porous boron δ-doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571
Electroluminescence in thin films, R.H. Mauch 92 (1996) 589
Si-based optical devices using porous materials, H. Mimura, T. Matsumoto and Y. Kanemitsu 92 (1996) 598

Magnesium oxide

Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47

Magnetic measurements

Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475

Manganese

Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
Effect of substrate–film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475

Mass spectroscopy

Surface reaction mechanism in MOCVD, J. Nishizawa, H. Sakuraba and T. Kurabayashi 92 (1996) 89

Metal–oxide–semiconductor structure (MOS)

Ultra-thin gate dielectrics grown by low-temperature processes for applications to ULSI devices, H.-L. Hwang, P.-C. Chen and K.Y.J. Hsu 92 (1996) 180
Application of irradiation-then-nitridation to improve the radiation hardness in MOS gate dielectrics, K.-C. Lee and J.-G. Hwu 92 (1996) 204
Rapid thermal post-metallization annealing effect on thin gate oxides, M.-J. Jeng, H.-S. Lin and J.-G. Hwu 92 (1996) 208

Metal–semiconductor interfaces

Chemical trends of barrier heights in metal–semiconductor contacts: on the theory of the slope parameter, W. Mönch 92 (1996) 367

Molecular dynamics

Atomistic dynamics of interfacial processes: films, junctions and nanostructures, U. Landman and W.D. Luedtke 92 (1996) 237

Molybdenum

The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
Novel epitaxial growth and magnetotransport characterization of single crystal $Co(11\bar{2}0)/Cr(100)$ superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480

Monte Carlo simulations

Computer simulation of nucleation on (001) Kossel crystal surface with and without diffusion, T.B. Tang 92 (1996) 257

Multilayers

A technological evolution from bulk crystalline age to multilayered thin film age in optoelectronic devices, Y. Hamakawa 92 (1996) 1
Recent advances in island and multilayer growth of metals on metals far from equilibrium, G. Vidali and H. Zeng 92 (1996) 11
Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wuu, M.L. Lee and T.Y. Lin 92 (1996) 626

Nickel

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and

their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74

Niobium

Effect of Nb metal ion in TiO_2 oxygen gas sensor, R.K. Sharma, M.C. Bhatnagar and G.L. Sharma 92 (1996) 647

Nitrides

Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
Effect of substrate–film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
Carbon nitride – prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656

Optical properties

The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
Diffusion length measurements on electrodeposited $CuInSe_2$ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wuu and T.Y. Lin 92 (1996) 387
Structural and optical properties of $Pd_{1-x}In_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391
Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404
Study of biochemical reactions in thin organic films by means of evanescent optical wave, T.I. Ksenevich, A.A. Beloglazov, P.I. Nikitin, N.A. Kalabina and S.Yu. Zaitsev 92 (1996) 426
Photoreflectance study of $GaAs/Al_{0.3}Ga_{0.7}As$ resonant asymmetric double quantum wells with Si δ-doping in side barriers, C.R. Lu, S.K. Du, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 543
Improvement of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gonda 92 (1996) 566

Oxidation

Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell, K. Sato, S. Nomura and Y. Inoue 92 (1996) 639

Oxides

Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
XPS, AES and LEED studies of Cu deposited on $Cr_2O_3(0001)$ surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513
Formation of bottom oxides in porous silicon films by anodic oxidation, C.H. Lee, C.C. Yeh, C.H. Lee and K.Y.J. Hsu 92 (1996) 621

Oxygen

The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
Oxygen etching of the Si(100)-(2 × 1) surface, Y. Wei, Y. Hong and I.S.T. Tsong 92 (1996) 491

Oxynitrides

Application of irradiation-then-nitridation to improve the radiation hardness in MOS gate dielectrics, K.-C. Lee and J.-G. Hwu 92 (1996) 204

Palladium

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Structural and optical properties of $Pd_{1-x}In_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391

Photoelectron emission microscopy

Photoemission spectromicroscopy and free electron laser spectroscopy of surfaces and interfaces, G. Margaritondo and Y. Hwu 92 (1996) 273

Photoelectron spectroscopy

Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47

XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong 92 (1996) 61

Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212

AES and SRUPS studies on surface passivation of GaAs by $(NH_4)_2S_x$ sulfurization techniques, J.T. Hsieh and H.L. Hwang 92 (1996) 222

XPS study of the reaction of the Si(100) surface with a C_2H_4 beam, T. Takagaki, Y. Igari, T. Takaoka and I. Kusunoki 92 (1996) 287

XPS, AES and LEED studies of Cu deposited on Cr_2O_3(0001) surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513

Surface fluorination of electrophotographic photoreceptors by plasma treatment for contact charging with a wet polymer roller, M. Satoh, S. Matsumoto, T. Higashiguchi, M. Matsuda, T. Muranoi, I. Kikuma, Y. Momose and M. Takeuchi 92 (1996) 635

Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell, K. Sato, S. Nomura and Y. Inoue 92 (1996) 639

Carbon nitride – prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656

Plasma processing

Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99

Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115

Ultra-thin gate dielectrics grown by low-temperature processes for applications to ULSI devices, H.-L. Hwang, P.-C. Chen and K.Y.J. Hsu 92 (1996) 180

Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wuu and T.Y. Lin 92 (1996) 387

Surface fluorination of electrophotographic photoreceptors by plasma treatment for contact charging with a wet polymer roller, M. Satoh, S. Matsumoto, T. Higashiguchi, M. Matsuda, T. Muranoi, I. Kikuma, Y. Momose and M. Takeuchi 92 (1996) 635

Platinum

Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74

Polymers

Study of biochemical reactions in thin organic films by means of evanescent optical wave, T.I. Ksenevich, A.A. Beloglazov, P.I. Nikitin, N.A. Kalabina and S.Yu. Zaitsev 92 (1996) 426

Simulation of polymer film and surface behaviour in a space environment, V.E. Skurat, E.A. Barbashev, Yu.I. Dorofeev, A.P. Nikiforov, M.M. Gorelova and A.I. Pertsyn 92 (1996) 441

An electrochemical impedance spectroscopy study of thin polymeric films, R. Borkowska, M. Siekierski and J. Przyłuski 92 (1996) 447

Quantum effects

A method to tune the island size and improve the uniformity for the in situ formation of InGaAs quantum dots on GaAs, S.-Z. Chang, T.-C. Chang and S.-C. Lee 92 (1996) 70

High quality quantum dots fabricated by molecular beam epitaxy, C.-P. Lee and D.-C. Liu 92 (1996) 519

Self-organized growth of InAs/GaAs quantum boxes, J.M. Moison, L. Leprince, F. Barthe, F. Houzay, N. Lebouché, J.M. Gérard and J.Y. Marzin 92 (1996) 526

Voltage-tunable far-infrared photodetector with a very large tuning range, Y. Huang and C. Lien 92 (1996) 537

Photoreflectance study of $GaAs/Al_{0.3}Ga_{0.7}As$ resonant asymmetric double quantum wells with Si δ-doping in side barriers, C.R. Lu, S.K. Du, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 543
Stimulated blue emission processes in $Zn_{1-x}Cd_xSe/ZnSe$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547
Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
Theory of room temperature quantized resistance steps in electroformed metal–a-Si:H–metal structures, J. Hajto, B. McAuley, A.J. Snell, G.H.W. Milburn and A.E. Owen 92 (1996) 579

Raman scattering

Low temperature growth of diamond-like films by cathodic arc plasma deposition, P.-L. Chen, M.-Y. Tsai and J.-S. Kao 92 (1996) 30
Characterization of low temperature GaAs grown by molecular beam epitaxy, W.C. Lee, T.M. Hsu, J.-I. Chyi, G.S. Lee, W.-H. Li and K.C. Lee 92 (1996) 66
Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
Pulsed-laser deposition of ''diamond-like'' carbon coating on $YBa_2Cu_3O_7$ high-T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457
Carbon nitride – prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656

Rhodium

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35

Scanning tunneling microscopy

High-temperature STM for atomic processes on semiconductor surfaces, M. Iwatsuki, T. Sato and Y. Yamamoto 92 (1996) 321
Oxygen etching of the Si(100)-(2 × 1) surface, Y. Wei, Y. Hong and I.S.T. Tsong 92 (1996) 491

Schottky barrier

Ultra accurate measurements of interface parameters with free-electron laser, C. Coluzza 92 (1996) 267
Schottky barrier formation for passivated semiconductor surfaces, R. Saiz-Pardo, R. Rincón and F. Flores 92 (1996) 362

Secondary ion mass spectrometry

Structural characterization of $BaTiO_3$ films by sol–gel method using mono-substituting chelating agent, W.-K. Kuo, J.-P. Wang and Y.-C. Ling 92 (1996) 155
Surfactant modified growth of $CuInSe_2$ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
Reliability study of sub-micron titanium silicide contacts, C.C. Lin, W.S. Chen, H.L. Hwang, K.Y.J. Hsu, H.K. Liou and K.N. Tu 92 (1996) 660

Selenium

Epitaxial growth of $ZnSe_xTe_{1-x}$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79
Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka 92 (1996) 132
Surfactant modified growth of $CuInSe_2$ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
Diffusion length measurements on electrodeposited $CuInSe_2$ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
Band lineup modification by Ge interlayer deposition at II–VI/III–V semiconductor heterojunctions, P. Rodríguez-Hernández, M. González-Diaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz 92 (1996) 408
Interface of $CuIn_{1-x}Ga_xSe_2/GaAs$ heterostructure, B.-H. Tseng, S.-B. Lin, G.-L. Gu and H.-Z. Hsu 92 (1996) 412

Stimulated blue emission processes in $Zn_{1-x}Cd_xSe/ZnSe$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547
Thin film photovoltaics, H.W. Schock 92 (1996) 606

Semiconductors

Theory of dipole generation at cleaved semiconductor surfaces, B. Chen and D. Haneman 92 (1996) 345
Schottky barrier formation for passivated semiconductor surfaces, R. Saiz-Pardo, R. Rincón and F. Flores 92 (1996) 362
Chemical trends of barrier heights in metal–semiconductor contacts: on the theory of the slope parameter, W. Mönch 92 (1996) 367
Semiconductor bond rupture phenomena and surface properties, D. Haneman, N.S. McAlpine, E. Busch and C. Kaalund 92 (1996) 484
Noise characteristics of an infrared hot-electron transistor, C.H. Kuan 92 (1996) 532
Novel light quantum and nuclear particle detectors based on the avalanche metal–resistivity layer–semiconductor structure, Z.Y. Sadygov, I.M. Zheleznykh and T.A. Kirillova 92 (1996) 575

Silica

Post cleaning of chemical mechanical polishing process, C.-W. Liu, B.-T. Dai and C.-F. Yeh 92 (1996) 176

Silicides

Reliability study of sub-micron titanium silicide contacts, C.C. Lin, W.S. Chen, H.L. Hwang, K.Y.J. Hsu, H.K. Liou and K.N. Tu 92 (1996) 660

Silicon

Stability of $BaTiO_3$ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
Study of Ag thin films deposited on porous silicon, T F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128
Growth of the thin film Cd–Si–As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
Porous silicon studied by Si L_{23} soft X-ray emission, R.S. Crisp, D. Haneman and R. Sabet-Dariani 92 (1996) 198
Application of irradiation-then-nitridation to improve the radiation hardness in MOS gate dielectrics, K.-C. Lee and J.-G. Hwu 92 (1996) 204
In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282
XPS study of the reaction of the Si(100) surface with a C_2H_4 beam, T. Takagaki, Y. Igari, T. Takaoka and I. Kusunoki 92 (1996) 287
Electron paramagnetic resonance measurements on porous silicon, T. Nakamura, K. Sasaki, K. Hayashi, H. Mimura and J. Kobayashi 92 (1996) 291
Ellipsometric study of thermal and laser annealed amorphous and microcrystalline silicon films, A.H. Jayatissa, M. Suzuki, Y. Nakanishi and Y. Hatanaka 92 (1996) 300
Interface phase transition as observed in ultra thin $FeSi_2$ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
High-temperature STM for atomic processes on semiconductor surfaces, M. Iwatsuki, T. Sato and Y. Yamamoto 92 (1996) 321
Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340

Surface electronic properties of GaSe-covered Si(111) upon UHV thermal desorption of the GaSe epitaxial layer, H. Reqqass, J.-P. Lacharme, C.A. Sébenne, M. Eddrief and V. Le Thanh 92 (1996) 357
Schottky barrier formation for passivated semiconductor surfaces, R. Saiz-Pardo, R. Rincón and F. Flores 92 (1996) 362
Investigation of the dosage effect on the activation of arsenic- and boron-implanted low-pressure chemical vapor deposition (LPCVD) amorphous-silicon films, F.-S. Wang, M.-J. Tsai, W.-K. Lai and H.-C. Cheng 92 (1996) 372
Refractive index behavior of boron-doped silica films by plasma-enhanced chemical vapor deposition, R.H. Horng, F. Chen, D.S. Wuu and T.Y. Lin 92 (1996) 387
PL properties of porous Si anodized with various light illuminations, H. Mimura, T. Matsumoto and Y. Kanemitsu 92 (1996) 396
Surface charge transfer in plastically deformed Si, B. Pohoryles and A. Morawski 92 (1996) 417
In situ radiotracer method for study of adsorption on semiconductor single crystal surfaces, M. Szklarczyk 92 (1996) 431
Oxygen etching of the Si(100)-(2 × 1) surface, Y. Wei, Y. Hong and I.S.T. Tsong 92 (1996) 491
First-principles calculations of Ga adatom structures for Ge(111) and Si(111) surfaces, C. Cheng and K. Kunc 92 (1996) 496
Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507
Diffusion phenomena in MBE grown Si/SiGe single quantum wells studied by PL and TEM measurements, H.P. Zeindl, S. Nilsson and E. Bugiel 92 (1996) 552
Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
Light emission from the porous boron δ-doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571
Theory of room temperature quantized resistance steps in electroformed metal–a-Si:H–metal structures, J. Hajto, B. McAuley, A.J. Snell, G.H.W. Milburn and A.E. Owen 92 (1996) 579
Si-based optical devices using porous materials, H. Mimura, T. Matsumoto and Y. Kanemitsu 92 (1996) 598
Thin film photovoltaics, H.W. Schock 92 (1996) 606
Correlation between light emission and dangling bonds in porous silicon, M. Shimasaki, Y. Show, M. Iwase, T. Izumi, T. Ichinohe, S. Nozaki and H. Morisaki 92 (1996) 617
Formation of bottom oxides in porous silicon films by anodic oxidation, C.H. Lee, C.C. Yeh, C.H. Lee and K.Y.J. Hsu 92 (1996) 621
Tungsten absorber on silicon membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665

Silicon carbide

XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong 92 (1996) 61

Silicon nitride

Tribochemical characterization of the lubrication film at the Si_3N_4/Si_3N_4 interface sliding in aqueous solutions, F. Honda and T. Saito 92 (1996) 651

Silicon oxide

The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193

Silver

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57

Solar cells

Influence of KCN treatment on $CuInS_2$ thin films, Y. Ogawa, A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232

Sputter deposition

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F.

Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
Stability of $BaTiO_3$ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
Structural and optical properties of $Pd_{1-x}In_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391
Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wuu, M.L. Lee and T.Y. Lin 92 (1996) 626
Carbon nitride – prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656

Sulphides

Influence of KCN treatment on $CuInS_2$ thin films, Y. Ogawa, A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232

Sulphur

Sprayed films of stannite Cu_2ZnSnS_4, N. Nakayama and K. Ito 92 (1996) 171
Adsorption of H_2S on GaP(001) surface and passivation effects studied by AES, LEED and XPS, Y. Fukuda, N. Sanada, M. Kuroda and Y. Suzuki 92 (1996) 212

Superconductivity

Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high-T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457
Investigation on origin of excess noise in superconducting and normal state BiSrCaCuO films, A.L. Li and I. Shih 92 (1996) 461

Superlattices

Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
Novel epitaxial growth and magnetotransport characterization of single crystal Co(11$\bar{2}$0)/Cr(100) superlattices on Mo buffer layers, J.C.A. Huang, Y.D. Yao, Y. Liou, S.F. Lee, W.T. Yang, C.P. Chang, S.Y. Liao and C.H. Lee 92 (1996) 480
Improvement of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, T. Ogura, K. Doi and S. Gonda 92 (1996) 566

Tantalum

Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wuu, M.L. Lee and T.Y. Lin 92 (1996) 626

Tellurium

Epitaxial growth of $ZnSe_xTe_{1-x}$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79

Thermal desorption

Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128

Thin films

Low temperature growth of diamond-like films by cathodic arc plasma deposition, P.-L. Chen, M.-Y. Tsai and J.-S. Kao 92 (1996) 30
Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Diamond-like coating prepared by pulsed laser sputtering of graphite in a high-vacuum environment, I.A. Bogonin, A.L. Karuzskii, N.N. Melnik, Yu.A. Mityagin, V.N. Murzin, A.A. Orlikovsky, A.V. Perestoronin, P.P. Sver-

bil, S.D. Tkachenko, A.V. Tsikunov, N.A. Volchkov and B.G. Zhurkin 92 (1996) 43
Structural and physical properties of Co films DC-bias-plasma-sputter-deposited on MgO(001), H. Qiu, T. Ohbuchi, H. Nakai and M. Hashimoto 92 (1996) 47
Stability of $BaTiO_3$ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
Study of Ag thin films deposited on porous silicon, T.F. Young, J.F. Liu, C.C. Wu, G.H. Fu and C.S. Chen 92 (1996) 57
XPS studies on SiC thin layers formed by ion implantation with a metal vapor vacuum arc ion source, H. Yan, R.W.M. Kwok and S.P. Wong 92 (1996) 61
Growth mechanism of Ni on Pt(110) at low temperature, C.S. Shern, J.S. Tsay and T. Fu 92 (1996) 74
Epitaxial growth of $ZnSe_xTe_{1-x}$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79
Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
Very low temperature polycrystalline silicon films with very large grains deposited for thin film transistor applications, K.C. Wang, T.R. Yew and H.L. Hwang 92 (1996) 99
Tribological properties of smooth diamond films, S.M. Pimenov, A.A. Smolin, E.D. Obraztsova, V.I. Konov, U. Bögli, A. Blatter, E.N. Loubnin, M. Maillat, A. Leijala, J. Burger and H.E. Hintermann 92 (1996) 106
Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
Characteristics of PECVD GaN thin films, C.H. Lee and C.T. Chen 92 (1996) 124
Ge deposition from digermane on the Si(100)-(2 × 1) surface, H.-C. Cho 92 (1996) 128
Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka 92 (1996) 132
Growth of the thin film Cd–Si–As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
Electrosynthesis of yttrium chalcogenides from a non-aqueous bath, U.K. Mohite and C.D. Lokhande 92 (1996) 151
Structural characterization of $BaTiO_3$ films by sol–gel method using mono-substituting chelating agent, W.-K. Kuo, J.-P. Wang and Y.-C. Ling 92 (1996) 155
The electrical and optical characteristics of GaAs on Si by modified flow rate modulation epitaxy, M.K. Lee, C.C. Hu, and C.Z. Hwang 92 (1996) 159
Characteristics of spray pyrolytic ZnO thin films, C.H. Lee and L.Y. Lin 92 (1996) 163
Fluorine doped tin oxide films from spray pyrolysis of stannous fluoride solutions, G.C. Morris and A.E. McElnea 92 (1996) 167
Sprayed films of stannite Cu_2ZnSnS_4, N. Nakayama and K. Ito 92 (1996) 171
The properties of SiO_2 films using direct photo-chemical vapor deposition on strained SiGe layers, C.T. Lin, S.J. Chang, D.K. Nayak and Y. Shiraki 92 (1996) 193
Surfactant modified growth of $CuInSe_2$ thin films, B.-H. Tseng, G.-W. Chang and G.-L. Gu 92 (1996) 227
Influence of KCN treatment on $CuInS_2$ thin films, Y. Ogawa, A. Jäger-Waldau, T.H. Hua, Y. Hashimoto and K. Ito 92 (1996) 232
Phenomenological approach in modeling of thin film nucleation from the liquid phase, T.V. Sakalo and S.A. Kukushkin 92 (1996) 261
In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282
Photoellipsometric studies on CdTe thin films, P.D. Paulson and V. Dutta 92 (1996) 295
Diffusion length measurements on electrodeposited $CuInSe_2$ cells, S.N. Qiu, C.X. Qiu and I. Shih 92 (1996) 306
Interface phase transition as observed in ultra thin $FeSi_2$ epilayers, J. Derrien, I. Berbezier, A. Ronda and J.Y. Natoli 92 (1996) 311
Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340
Coalescence of cylindrical islands on the crystal surface accompanied by correlated changes of their heights and radii, T.V. Sakalo and S.A. Kukushkin 92 (1996) 350

Structural and electrical properties of excimer laser deposited PLZT thin films, H.-F. Cheng 92 (1996) 378
Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
Structural and optical properties of $Pd_{1-x}In_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391
The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
Study of the internal electric fields across the interfaces in the GaAs/(Al,Ga)As microstructures, C.R. Lu, C.L. Chang, C.H. Liou, J.R. Anderson, D.R. Stone and R.A. Wilson 92 (1996) 404
Electrochromic behavior of amorphous cobaltphthalocyanine thin films, M. Masui, T. Ogawa and M. Takeuchi 92 (1996) 421
Study of biochemical reactions in thin organic films by means of evanescent optical wave, T.I. Ksenevich, A.A. Beloglazov, P.I. Nikitin, N.A. Kalabina and S.Yu. Zaitsev 92 (1996) 426
Simulation of polymer film and surface behaviour in a space environment, V.E. Skurat, E.A. Barbashev, Yu.I. Dorofeev, A.P. Nikiforov, M.M. Gorelova and A.I. Pertsyn 92 (1996) 441
An electrochemical impedance spectroscopy study of thin polymeric films, R. Borkowska, M. Siekierski and J. Przyłuski 92 (1996) 447
Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452
Pulsed-laser deposition of "diamond-like" carbon coating on $YBa_2Cu_3O_7$ high-T_c superconductor films, A.L. Karuzskii, N.N. Melnik, V.N. Murzin, V.S. Nozdrin, A.V. Perestoronin, N.A. Volchkov and B.G. Zhurkin 92 (1996) 457
Investigation on origin of excess noise in superconducting and normal state BiSrCaCuO films, A.L. Li and I. Shih 92 (1996) 461
Effect of substrate–film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
Structural evolution and atomic structure of ultrahigh vacuum deposited Au thin films on silicon at low temperatures, C.R. Chen and L.J. Chen 92 (1996) 507
XPS, AES and LEED studies of Cu deposited on Cr_2O_3(0001) surfaces, Q. Guo, L. Gui, P.J. Møller and K. Binau 92 (1996) 513
Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
Electroluminescence in thin films, R.H. Mauch 92 (1996) 589
Thin film photovoltaics, H.W. Schock 92 (1996) 606
Formation of bottom oxides in porous silicon films by anodic oxidation, C.H. Lee, C.C. Yeh, C.H. Lee and K.Y.J. Hsu 92 (1996) 621
Properties of multilayered thin films for thermal ink-jet printing devices, D.S. Wuu, M.L. Lee and T.Y. Lin 92 (1996) 626
Solar cells from thin films prepared by periodic pulse electrodeposition, G.C. Morris and R.J. Vanderveen 92 (1996) 630
Gas sensitive properties of copperphthalocyanine thin films, M. Masui, M. Sasahara, T. Wada and M. Takeuchi 92 (1996) 634
Carbon nitride – prospects for ultimate performance of superhard materials, S.A. Uglov, V.E. Shub, A.A. Beloglazov and V.I. Konov 92 (1996) 656
Tungsten absorber on silicon membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665

Tin

Sprayed films of stannite Cu_2ZnSnS_4, N. Nakayama and K. Ito 92 (1996) 171

Tin oxide

Fluorine doped tin oxide films from spray pyrolysis of stannous fluoride solutions, G.C. Morris and A.E. McElnea 92 (1996) 167

Titanium

Reliability study of sub-micron titanium silicide contacts, C.C. Lin, W.S. Chen, H.L. Hwang, K.Y.J. Hsu, H.K. Liou and K.N. Tu 92 (1996) 660

Titanium dioxide

Effect of Nb metal ion in TiO_2 oxygen gas sensor, R.K. Sharma, M.C. Bhatnagar and G.L. Sharma 92 (1996) 647

Titanium nitride

Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335

Titanium oxide

Stability of $BaTiO_3$ thin films on Si, L.H. Chang and W.A. Anderson 92 (1996) 52
Structural characterization of $BaTiO_3$ films by sol–gel method using mono-substituting chelating agent, W.-K. Kuo, J.-P. Wang and Y.-C. Ling 92 (1996) 155

Transition metals

Electrocatalytic activities of proton-exchanged layered oxides for the anodic oxidation on the solid oxide fuel cell, K. Sato, S. Nomura and Y. Inoue 92 (1996) 639

Tribology

Tribological properties of smooth diamond films, S.M. Pimenov, A.A. Smolin, E.D. Obraztsova, V.I. Konov, U. Bögli, A. Blatter, E.N. Loubnin, M. Maillat, A. Leijala, J. Burger and H.E. Hintermann 92 (1996) 106

Tungsten

Tungsten absorber on silicon membrane, D.C. Li, C.S. Yoo and C.Y. Sun 92 (1996) 665

Tunneling

Magnetostochastic resonance as a new method for investigations of surface and thin film magnetism, A.N. Grigorenko and P.I. Nikitin 92 (1996) 466

Vanadium

The determination of the average compositions of amorphous interlayers in the V/Si system using a buried ultrathin oxide layer and a capping Mo layer to define the reference planes for interdiffusion, J.H. Lin and L.J. Chen 92 (1996) 340

Water

A theoretical analysis of the molecular and dissociative adsorption of H_2O on GaAs(110), R. Rincón, F.J. García-Vidal and F. Flores 92 (1996) 216

X-ray diffraction

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Effects of substrate cleaning and film thickness on the epitaxial growth of ultrahigh vacuum deposited Cu thin films on (001)Si, C.S. Liu and L.J. Chen 92 (1996) 84
Textured diamond growth by microwave plasma chemical vapor deposition, Y. Liou 92 (1996) 115
Disordered Si/SiGe superlattices grown by ultrahigh vacuum chemical vapor deposition, T.-C. Chang, W.-K. Yeh, C.-Y. Chang, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 119
Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka 92 (1996) 132
Growth of the thin film Cd–Si–As system by metalorganic chemical vapor deposition, H. Kayama, Y. Noda and Y. Furukawa 92 (1996) 142
Electrosynthesis of yttrium chalcogenides from a non-aqueous bath, U.K. Mohite and C.D. Lokhande 92 (1996) 151
Characteristics of spray pyrolytic ZnO thin films, C.H. Lee and L.Y. Lin 92 (1996) 163
Sprayed films of stannite Cu_2ZnSnS_4, N. Nakayama and K. Ito 92 (1996) 171
Interdiffusion and reactions in the Cu/TiN/Si thin film system, Y.S. Gong, J.-C. Lin and C. Lee 92 (1996) 335
Structural characterization of epitaxial ferromagnetic MnSb layers grown by hot-wall epitaxy, H. Tatsuoka, H. Kuwabara, M. Oshita, Y. Nakanishi, T. Nakamura and H. Fujiyasu 92 (1996) 382
Structural and optical properties of $Pd_{1-x}In_x$ thin films, W.T. Wu, P.E. Schmid and F. Lévy 92 (1996) 391
The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400

Electrochromic behavior of amorphous cobaltphthalocyanine thin films, M. Masui, T. Ogawa and M. Takeuchi 92 (1996) 421
Effect of substrate–film interface on magnetic properties of Mn_4N films, K.-M. Ching, W.-D. Chang and T.-S. Chin 92 (1996) 471
Coercivity of γ-$(Fe_{0.74}Mn_{0.15}Co_{0.11})_2O_3$ thin films by dc reactive magnetron sputtering, W.-D. Chang and T.-S. Chin 92 (1996) 475
Dopant activation and strain relaxation in P-implanted metastable pseudomorphic $Ge_{0.12}Si_{0.88}$ grown on Si(100), D.Y.C. Lie, N.D. Theodore and J.H. Song 92 (1996) 557
Light emission from the porous boron δ-doped Si superlattice, T.-C. Chang, W.-K. Yeh, M.-Y. Hsu, C.-Y. Chang, C.-P. Lee, T.-G. Jung, W.-C. Tsai, G.-W. Huang and Y.-J. Mei 92 (1996) 571

X-ray emission

Glow discharge sputtering deposition of thin films of Ag, Cr, Cu, Ni, Pd, Rh and their binary alloys onto NaCl and MgO. Experimental parameters and epitaxy, F. Reniers, M.P. Delplancke, A. Asskali, V. Rooryck and O. Van Sinay 92 (1996) 35
Porous silicon studied by SiL_{23} soft X-ray emission, R.S. Crisp, D. Haneman and R. Sabet-Dariani 92 (1996) 198
Tribochemical characterization of the lubrication film at the Si_3N_4/Si_3N_4 interface sliding in aqueous solutions, F. Honda and T. Saito 92 (1996) 651

X-ray scattering

In situ X-ray reflectivity measurement of thin film growth during vacuum deposition, C.-H. Lee and S.-Y. Tseng 92 (1996) 282

X-ray spectroscopy

Characterization of low temperature GaAs grown by molecular beam epitaxy, W.C. Lee, T.M. Hsu, J.-I. Chyi, G.S. Lee, W.-H. Li and K.C. Lee 92 (1996) 66

Yttrium

Electrosynthesis of yttrium chalcogenides from a non-aqueous bath, U.K. Mohite and C.D. Lokhande 92 (1996) 151
Electrical properties of laser deposited $YBa_2Cu_3O_{7-\delta}$ films on silicon wafers, F.Y. Chuang, C.T. Lin, C.Y. Sun, H.F. Cheng and I.N. Lin 92 (1996) 452

Zinc

Epitaxial growth of $ZnSe_xTe_{1-x}$ by the VPE method and its photoluminescence, K. Mochizuki, H. Oguri, T. Kyotani and M. Isshiki 92 (1996) 79
Growth of ZnSe thin films by radical assisted MOCVD method, T. Aoki, M. Morita, S. Wickramanayaka, Y. Nakanishi and Y. Hatanaka 92 (1996) 132
Growth of Zn δ-doped $Al_xGa_{1-x}As$ (x = 0–0.65) by low pressure metal organic vapour phase epitaxy, G. Li and C. Jagadish 92 (1996) 138
Sprayed films of stannite Cu_2ZnSnS_4, N. Nakayama and K. Ito 92 (1996) 171
The influence of residual O_2 gas in vacuum on the structural and luminescent properties of ZnF_2:Mn thin films, Y. Nakanishi, S. Naito, T. Nakamura, Y. Hatanaka and G. Shimaoka 92 (1996) 400
Band lineup modification by Ge interlayer deposition at II–VI/III–V semiconductor heterojunctions, P. Rodríguez-Hernández, M. González-Diaz, M. Fuentes-Cabrera, A. Mujica and A. Muñoz 92 (1996) 408
Stimulated blue emission processes in $Zn_{1-x}Cd_xSe/ZnSe$ multi-quantum wells, J.Y. Jen, T. Tsutsumi, I. Souma, Y. Oka, J.R. Anderson and M. Gorska 92 (1996) 547

Zinc oxide

Characteristics of spray pyrolytic ZnO thin films, C.H. Lee and L.Y. Lin 92 (1996) 163